Mu Wen Chuan

List of Publications by Year in descending order

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Version: 2024-02-01

		1478458	1474186	
18	84	6	9	
papers	citations	h-index	g-index	
18	18	18	57	
all docs	docs citations	times ranked	citing authors	

#	Article	IF	CITATIONS
1	2D Honeycomb Silicon: A Review on Theoretical Advances for Silicene Field-Effect Transistors. Current Nanoscience, 2020, 16, 595-607.	1.2	12
2	Electronic properties and carrier transport properties of low-dimensional aluminium doped silicene nanostructure. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 116, 113731.	2.7	11
3	A review of the top of the barrier nanotransistor models for semiconductor nanomaterials. Superlattices and Microstructures, 2020, 140, 106429.	3.1	11
4	Electronic properties of graphene nanoribbons with line-edge roughness doped with nitrogen and boron. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 117, 113841.	2.7	9
5	Carrier transport of rough-edged doped GNRFETs with metal contacts at various channel widths. Superlattices and Microstructures, 2020, 143, 106548.	3.1	7
6	Impact of phonon scattering mechanisms on the performance of silicene nanoribbon field-effect transistors. Results in Physics, 2021, 29, 104714.	4.1	7
7	Performance metrics of current transport in pristine graphene nanoribbon field-effect transistors using recursive non-equilibrium Green's function approach. Superlattices and Microstructures, 2020, 145, 106624.	3.1	6
8	Compact device modelling of interface trap charges with quantum capacitance in MoS ₂ -based field-effect transistors. Semiconductor Science and Technology, 2020, 35, 045023.	2.0	4
9	A low cost spectroscopy with Raspberry Pi for soil macronutrient monitoring. Telkomnika (Telecommunication Computing Electronics and Control), 2019, 17, 1867.	0.8	4
10	Modeling of lightly-doped drain and source contact with boron and nitrogen in graphene nanoribbon. Chinese Journal of Physics, 2019, 62, 258-273.	3.9	3
11	Device performance of silicene nanoribbon field-effect transistor under ballistic transport. , 2020, , .		3
12	Carrier statistics of highly doped armchair graphene nanoribbons with edge disorder. Superlattices and Microstructures, 2020, 139, 106404.	3.1	3
13	Electronic properties of silicene nanoribbons using tight-binding approach. , 2019, , .		2
14	Device performances analysis of p-type doped silicene-based field effect transistor using SPICE-compatible model. PLoS ONE, 2022, 17, e0264483.	2.5	2
15	The productiveness of Bootstrap simulator in evaluating the accuracy parameters of measurement system for ball screw. Journal of Physics: Conference Series, 2019, 1366, 012129.	0.4	0
16	Semi-analytical modelling and evaluation of uniformly doped silicene nanotransistors for digital logic gates. PLoS ONE, 2021, 16, e0253289.	2.5	0
17	Influence of single vacancy defect at varying length on electronic properties of zigzag graphene nanoribbons. Indonesian Journal of Electrical Engineering and Informatics, 2019, 7, .	0.3	O
18	Electronic properties of zigzag silicene nanoribbons with single vacancy defect. Indonesian Journal of Electrical Engineering and Computer Science, 2020, 19, 76.	0.8	0